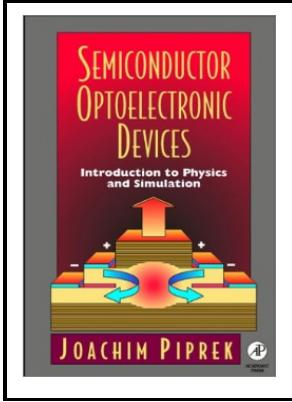


Semiconductor device physics and simulation

Plenum Press - 2.1 Classical Semiconductor Device Equations

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